**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

## 2. Features and benefits

- · Low reverse recovery current and low thermal resistance
- Reduces switching losses in associated MOSFET

# 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions Values			Unit		
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		600		V		
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 93$ °C; Fig. 1; Fig. 2	10		А		
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 μs; $T_{mb}$ ≤ 93 °C; square-wave pulse	20		А		
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	65 71 Min Typ Max		А		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions			Unit		
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	2	2.5	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.4	1.8	V
Dynamic	characteristics					1	
t <sub>rr</sub>	reverse recovery time	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	18	-	ns

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	001aaa020

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BYC10D-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

# 7. Marking

## **Table 4. Marking codes**

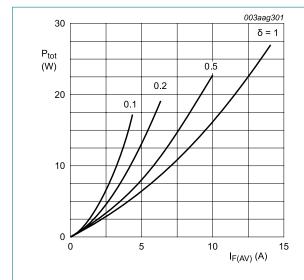
Type number	Marking codes
BYC10D-600	BYC10D-600

# 8. Limiting values

### **Table 5. Limiting values**

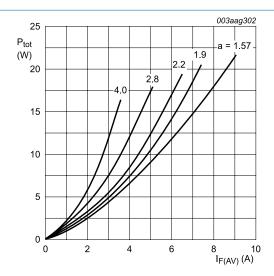
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{RWM}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	DC	500	V
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 93$ °C; Fig. 1; Fig. 2	10	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 93 °C; square-wave pulse	20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	65	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	71	А
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C



 $\begin{aligned} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.987 \text{ V}; \text{ R}_s = 0.065 \text{ }\Omega \end{aligned}$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 0.987 V;  $R_s$  = 0.065  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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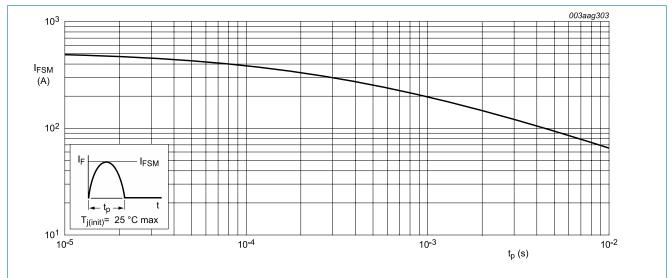


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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## 9. Thermal characteristics

### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig 4	-	-	2.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

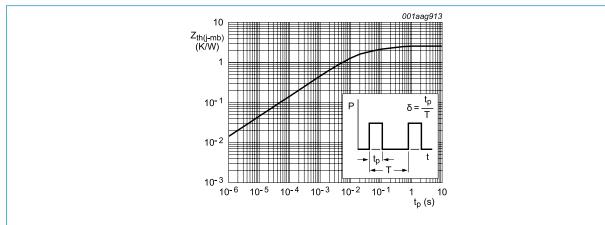
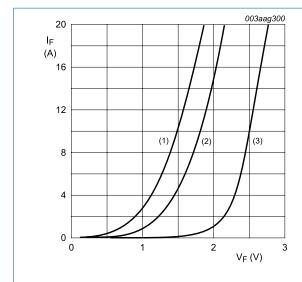


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

## 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub> for	forward voltage	I <sub>F</sub> = 20A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.7	2.2	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	2	2.5	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.4	1.8	V
I <sub>R</sub> re	reverse current	V <sub>R</sub> = 600 V	-	9	200	μA
		V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C	-	1.1	3	mA
Dynamic	characteristics			'		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 6}}{}$	-	15	30	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	18	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 6$	-	3	7.5	А
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 6$	-	9.5	12	А
V <sub>FR</sub>	forward recovery voltage	$I_F = 10 \text{ A}; \text{ dI}_F/\text{dt} = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; \frac{\text{Fig. 7}}{2}$	-	8	11	V



(1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

 $V_o = 0.987 \text{ V}; R_s = 0.065 \Omega$ 

Fig. 5. Forward current as a function of forward voltage

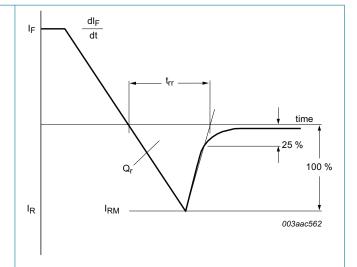
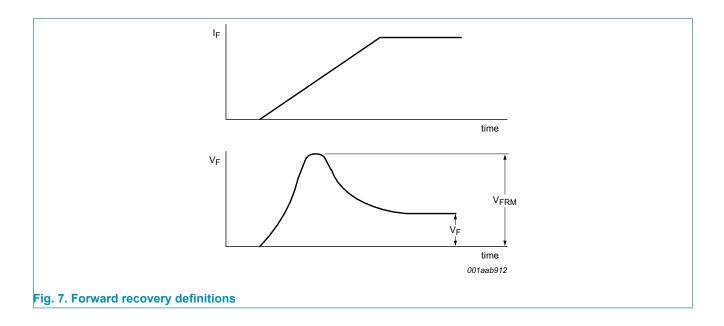


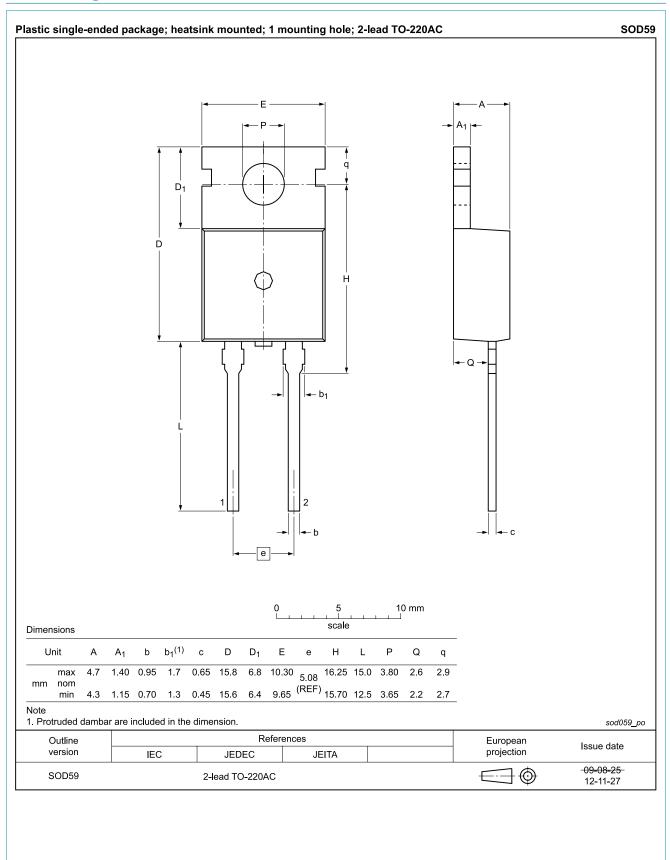
Fig. 6. Reverse recovery definitions; ramp recovery

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# 11. Package outline



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**BYC10D-600** 

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# 12. Revision history

### **Table 8. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYC10D-600 v.2	20180223	Product data sheet	-	BYC10D-600 v.1			
Modifications: Change from NXP version to WeEn version							
BYC10D-600 v.1	20110628	Product data sheet	-	-			

## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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